

## ENGR 305 – Homework 1

**3.1** Use the expression in Eq. (3.2), with

$$B = 7.3 \times 10^{15} \text{ cm}^{-3} \text{K}^{-3/2};$$

$$k = 8.62 \times 10^{-5} \text{ eV/K}; \text{ and } E_g = 1.12 \text{ V}$$

we have

$$T = -55^\circ\text{C} = 218 \text{ K}$$

$$n_i = 2.68 \times 10^6 \text{ cm}^{-3}; N/n_i$$

$$= 1.9 \times 10^{16} \text{ and } n_i/N = 5.36 \times 10^{-17}$$

That is, one out of every  $1.9 \times 10^{16}$  silicon atoms is ionized at this temperature.

$$T = 0^\circ\text{C} = 273 \text{ K}$$

$$n_i = 1.52 \times 10^9 \text{ cm}^{-3}; N/n_i$$

$$= 3.3 \times 10^{13} \text{ and } n_i/N = 3.04 \times 10^{-14}$$

$$T = 20^\circ\text{C} = 293 \text{ K}$$

$$n_i = 8.60 \times 10^9 \text{ cm}^{-3}; N/n_i$$

$$= 5.8 \times 10^{12} \text{ and } n_i/N = 1.72 \times 10^{-13}$$

$$T = 75^\circ\text{C} = 348 \text{ K}$$

$$n_i = 3.70 \times 10^{11} \text{ cm}^{-3}; N/n_i$$

$$= 1.4 \times 10^{11} \text{ and } n_i/N = 7.4 \times 10^{-12}$$

$$T = 125^\circ\text{C} = 398 \text{ K}$$

$$n_i = 4.72 \times 10^{12} \text{ cm}^{-3}; N/n_i$$

$$= 1.1 \times 10^{10} \text{ and } n_i/N = 9.44 \times 10^{-11}$$

**3.4** Since  $N_A \gg n_i$ , we can write

$$p_p \approx N_A = 2 \times 10^{18} \text{ cm}^{-3}$$

Using Eq. (3.3), we have

$$n_p = n_i^2/p_p$$

$$= 112.5 \text{ cm}^{-3}$$

**3.7 (a)** The resistivity of silicon is given by Eq. (3.17).

For intrinsic silicon,

$$p = n = n_i = 1.5 \times 10^{10} \text{ cm}^{-3}$$

Using  $\mu_n$

$$= 1350 \text{ cm}^2/\text{V} \cdot \text{s} \text{ and}$$

$\mu_p = 480 \text{ cm}^2/\text{V} \cdot \text{s}$ , and  $q = 1.6 \times 10^{-19} \text{ C}$  we have

$$\rho = 2.28 \times 10^5 \Omega\text{-cm}.$$

Using  $R = \rho \cdot L/A$

with  $L = 0.0015 \text{ cm}$  and

$$A = 3 \times 10^{-8} \text{ cm}^2, \text{ we have}$$

$$R = 11.4 \times 10^9 \Omega.$$

$$(b) n_n \approx N_D = 5 \times 10^{16} \text{ cm}^{-3};$$

$$p_n = n_i^2/n_n$$

$$= 4.5 \times 10^3 \text{ cm}^{-3}$$

Using  $\mu_n = 1200 \text{ cm}^2/\text{V} \cdot \text{s}$  and

$\mu_p = 400 \text{ cm}^2/\text{V} \cdot \text{s}$ , we have

$$\rho = 0.10 \Omega\text{-cm}; R = 5 \text{ k}\Omega.$$

$$(c) n_n \approx N_D = 5 \times 10^{18} \text{ cm}^{-3};$$

$$p_n = n_i^2/n_n$$

$$= 45 \text{ cm}^{-3}$$

Using  $\mu_n = 1200 \text{ cm}^2/\text{V} \cdot \text{s}$  and

$\mu_p = 400 \text{ cm}^2/\text{V} \cdot \text{s}$ , we have

$$\rho = 1.0 \times 10^{-3} \Omega\text{-cm}; R = 50 \Omega.$$

As expected, since  $N_D$  is increased by 100, the resistivity decreases by the same factor.

$$(d) p_p \approx N_A = 5 \times 10^{16} \text{ cm}^{-3}; n_p = n_i^2/n_n$$

$$= 4.5 \times 10^3 \text{ cm}^{-3}$$

$$\rho = 0.31 \Omega\text{-cm}; R = 15.63 \text{ k}\Omega$$

(e) Since  $\rho$  is given to be  $2.8 \times 10^{-6} \Omega\text{-cm}$ , we directly calculate  $R = 0.14 \Omega$ .

**3.14** From Table 3.1,

$$V_T \text{ at } 300 \text{ K} = 25.9 \text{ mV}$$

Using Eq. (3.21), built-in voltage  $V_0$  is obtained:

$$V_0 = V_T \ln \left( \frac{N_A N_D}{n_i^2} \right) = 25.9 \times 10^{-3} \times \ln \left( \frac{10^{17} \times 10^{16}}{(1.5 \times 10^{10})^2} \right) = 0.754V$$

Depletion width

$$W = \sqrt{\frac{2\epsilon_s}{q} \left( \frac{1}{N_A} + \frac{1}{N_D} \right) V_0} \quad \text{Eq. (3.25)}$$

$$W = \sqrt{\frac{2 \times 1.04 \times 10^{-12}}{1.6 \times 10^{-19}} \left( \frac{1}{10^{17}} + \frac{1}{10^{16}} \right) \times 0.754}$$

$$= 0.328 \times 10^{-4} \text{ cm} = 0.328 \mu\text{m}$$

Use Eqs. (3.26) and (3.27) to find  $x_n$  and  $x_p$ :

$$x_n = W \frac{N_D}{N_A + N_D} = 0.328 \mu\text{m} \times \frac{10^{17}}{10^{17} + 10^{16}} = 0.298 \mu\text{m}$$

$$x_p = W \frac{N_A}{N_A + N_D} = 0.328 \mu\text{m} \times \frac{10^{16}}{10^{17} + 10^{16}} = 0.03 \mu\text{m}$$

Use Eq. (3.28) to calculate charge stored on either side:

$$Q_J = Aq \left( \frac{N_A N_D}{N_A + N_D} \right) W, \text{ where junction area}$$

$$A = 10 \mu\text{m}^2 = 10 \times 10^{-8} \text{ cm}^2$$

$$Q_J = 10 \times 10^{-8} \times 1.6 \times 10^{-19} \left( \frac{10^{17} 10^{16}}{10^{17} + 10^{16}} \right) \times 0.328 \times 10^{-4}$$

$$\text{Hence, } Q_J = 4.8 \times 10^{-15} C$$

**3.20** There is a 2-V reverse bias applied across the junction of problem 3.14.

The built-in potential  $V_0$  remains the same;  $V_0 = 0.754 \text{ V}$ .

Use equation (3.30) for  $W$ ,

$$W = \sqrt{\frac{2\epsilon_s}{q} \left( \frac{1}{N_A} + \frac{1}{N_D} \right) (V_0 + V_R)} = \sqrt{\frac{2 \times 1.04 \times 10^{-12}}{1.6 \times 10^{-19}} \left( \frac{1}{10^{17}} + \frac{1}{10^{16}} \right) \times (0.754 + 2)} = 0.627 \mu\text{m}$$

Use equation (3.31) for  $Q_J$

$$Q_J = A \sqrt{2\epsilon_s q \left( \frac{N_A N_D}{N_A + N_D} \right) (V_0 + V_R)} =$$

$$10 \times 10^{-8} \sqrt{2 \times 1.04 \times 10^{-12} \times 1.6 \times 10^{-19} \left( \frac{10^{17} 10^{16}}{10^{17} + 10^{16}} \right) (2.754)} = 9.13 \times 10^{-15} C$$